

EL - 325

The EL - 325 is a GaAs IRED mounted in a low profile clear epoxy package. This IRED is both compact and easy to mount.

**FEATURES**

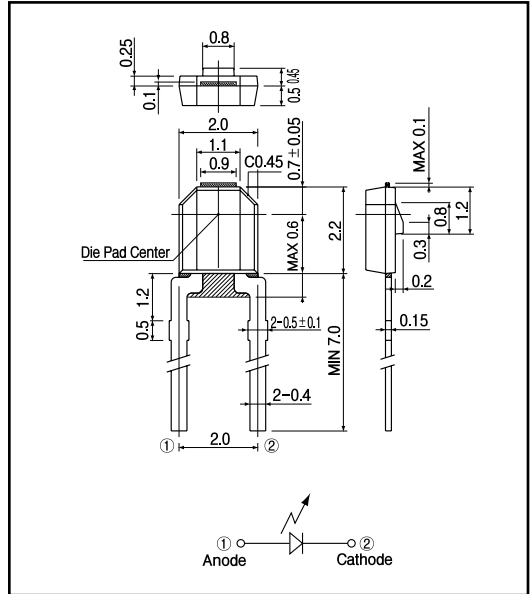
- Ultra compact
- Low profile
- Snap- in mount is possible

**APPLICATIONS**

- Photointerrupters
- Optical equipment

**DIMENSIONS**

(Unit : mm)



**MAXIMUM RATINGS**

(Ta=25 )

Item	Symbol	Rating	Unit
Reverse voltage	$V_R$	5	V
Forward current	$I_F$	50	mA
Power dissipation	$P_D$	100	mW
Pulse forward current <sup>*1</sup>	$I_{FP}$	0.5	A
Operating temp.	$T_{opr.}$	- 25 + 85	
Storage temp.	$T_{stg.}$	- 30 + 85	
Soldering temp. <sup>*2</sup>	$T_{sol.}$	260	

\*1. pulse width :  $t_w$  100  $\mu$ sec, period :  $T=10$ msec.

\*2. For MAX.5 seconds at the position of 2 mm from the package

**ELECTRO-OPTICAL CHARACTERISTICS**

(Ta=25 )

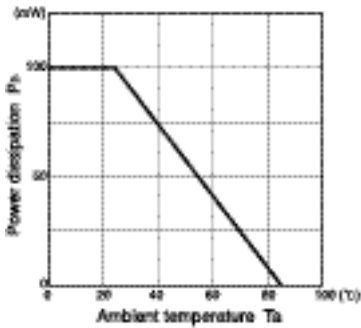
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	$V_F$	$I_F=50$ mA			1.6	V
Reverse current	$I_R$	$V_R=5$ V			10	$\mu$ A
Peak emission wavelength	$\lambda_p$	$I_F=50$ mA		940		nm
Spectral bandwidth		$I_F=50$ mA		50		nm
Radiant intensity <sup>*3</sup>	$P_D$	$I_F=50$ mA		0.7		mW/sr
Half angle				$\pm 50$		deg.

\*3. Measured by tester of KODENSHI CORP.

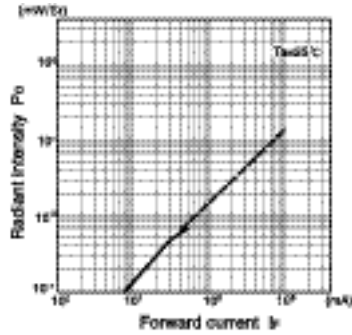
Infrared Emitting Diodes(GaAs)

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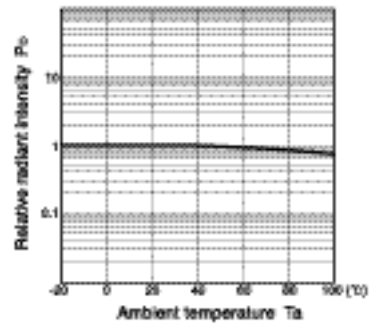
**Power dissipation Vs. Ambient temperature**



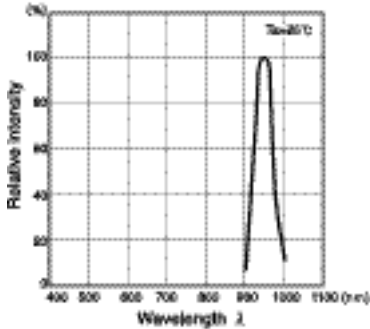
**Radiant intensity Vs. Forward current**



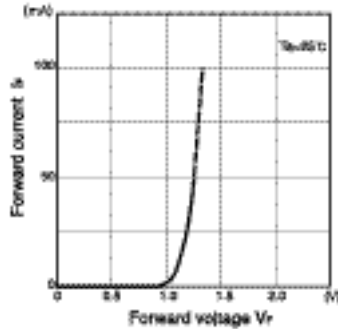
**Relative radiant intensity Vs. Ambient temperature**



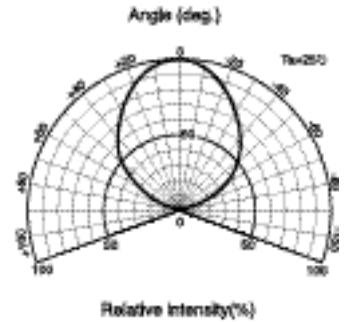
**Relative intensity Vs. Wavelength**



**Forward current vs. Forward voltage**



**Radiant Pattern**



**Relative radiant intensity Vs. Distance**

